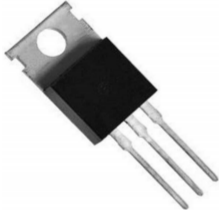
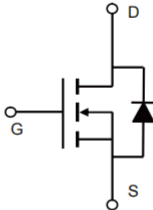


Description

<p><b>Features</b></p> <ul style="list-style-type: none"> <li>● 400V,6A</li> <li style="padding-left: 20px;"><math>R_{DS(ON)} &lt; 1.1\Omega @ V_{GS} = 10V</math></li> <li>● Fast Switching</li> <li>● Improved dv/dt Capability</li> </ul>	<p><b>Application</b></p> <ul style="list-style-type: none"> <li>● Load Switch</li> <li>● PWM Application</li> <li>● Power management</li> </ul>
 <p>TO-220C</p>	 <p>Schematic Diagram</p>

**Absolute Maximum Ratings** ( $T_C=25^\circ C$  unless otherwise specified)

Symbol	Parameter	Max.	Units
$V_{DSS}$	Drain-Source Voltage	400	V
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Continuous Drain Current	$T_C = 25^\circ C$	6
		$T_C = 100^\circ C$	3.9
$I_{DM}$	Pulsed Drain Current <sup>note1</sup>	24	A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>note2</sup>	80	mJ
$P_D$	Power Dissipation	$T_C = 25^\circ C$	54
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.3	$^\circ C / W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ C / W$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ C$

**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	400	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 400V, V_{GS} = 0V,$ $T_J = 25^{\circ}\text{C}$	-	-	1	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 30V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS} = 10V, I_D = 3A$	-	0.95	1.1	$\Omega$
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0\text{MHz}$	-	596	-	pF
$C_{oss}$	Output Capacitance		-	79	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	11	-	pF
$Q_g$	Total Gate Charge	$V_{DD} = 320V, I_D = 6A,$ $V_{GS} = 10V$	-	12.6	-	nC
$Q_{gs}$	Gate-Source Charge		-	4.1	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	4	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 200V, I_D = 6A,$ $R_G = 10\Omega$	-	14	-	ns
$t_r$	Turn-on Rise Time		-	20	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	31	-	ns
$t_f$	Turn-off Fall Time		-	12	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	6	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	24	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_{SD} = 6A$	-	-	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0V, I_S = 6A,$ $di/dt = 100A/\mu s$	-	240	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	1.2	-	$\mu C$

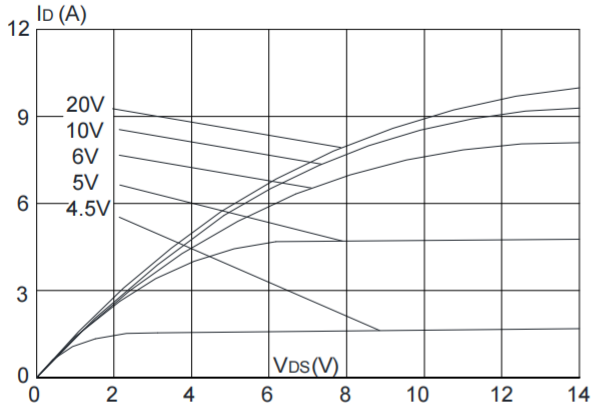
Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition:  $T_J = 25^{\circ}\text{C}, V_{DD} = 50V, V_G = 10V, L = 10\text{mH}, I_{AS} = 4A$

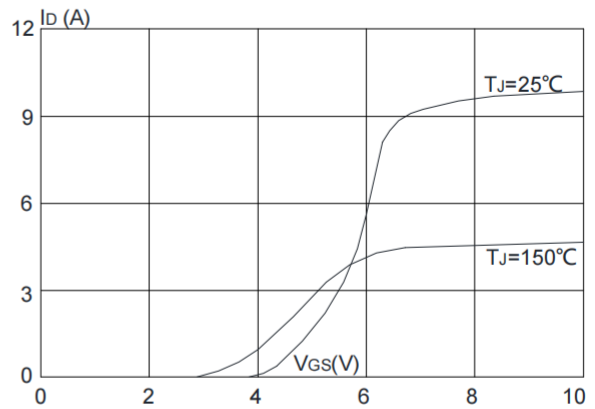
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 1\%$

## Typical Performance Characteristics

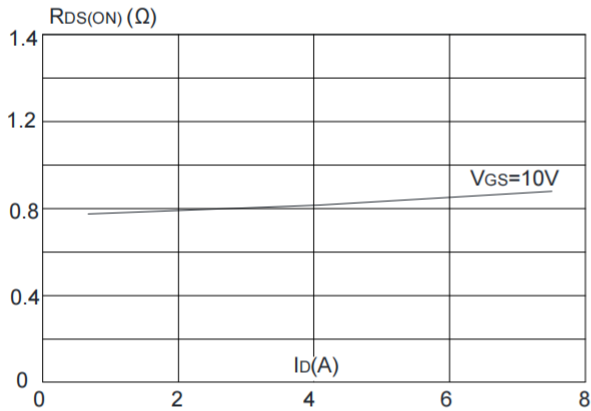
**Figure 1: Output Characteristics**



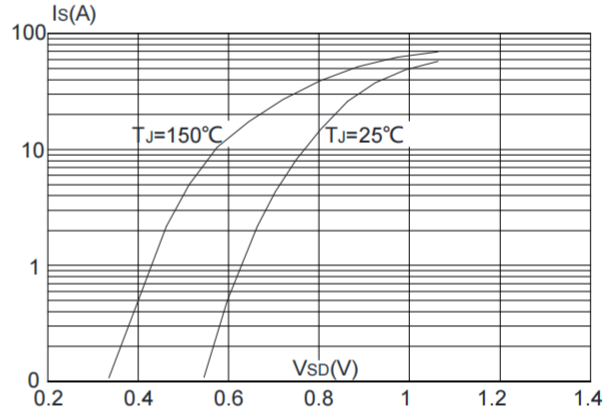
**Figure 2: Typical Transfer Characteristics**



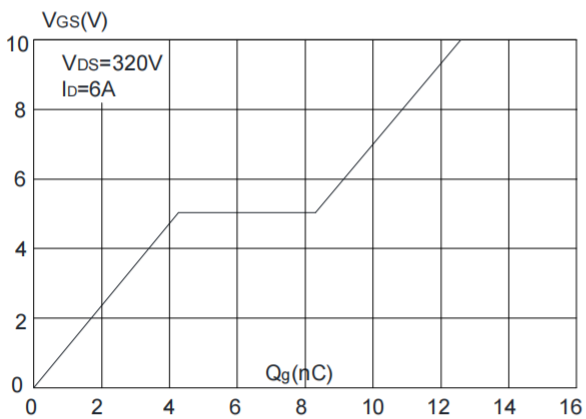
**Figure 3: On-resistance vs. Drain Current**



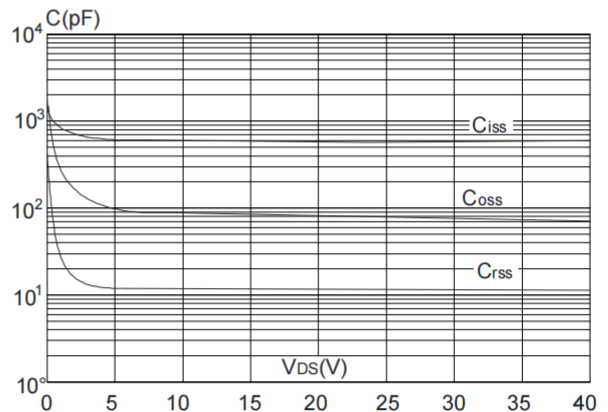
**Figure 4: Body Diode Characteristics**



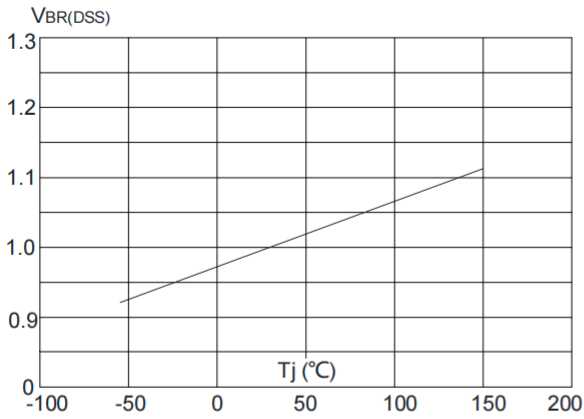
**Figure 5: Gate Charge Characteristics**



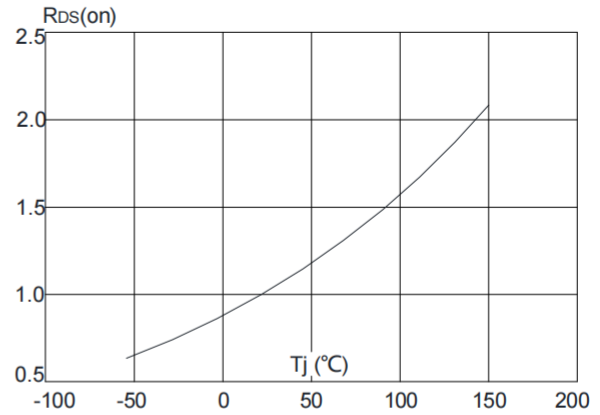
**Figure 6: Capacitance Characteristics**



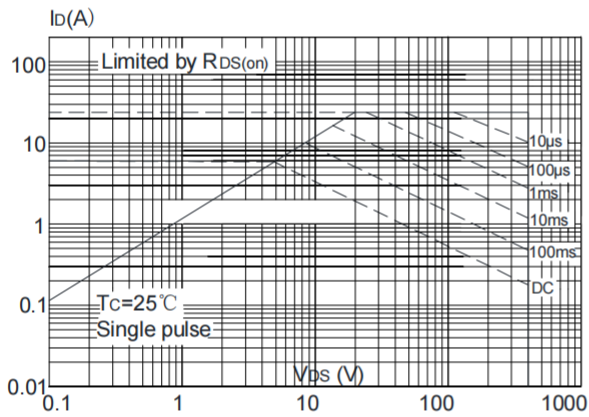
**Figure 7: Normalized Breakdown Voltage vs. Junction Temperature**



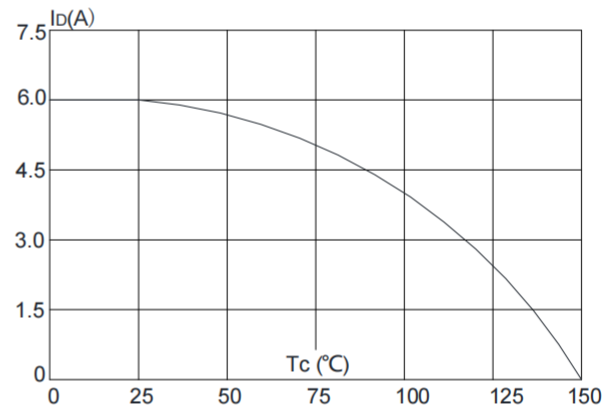
**Figure 8: Normalized on Resistance vs. Junction Temperature**



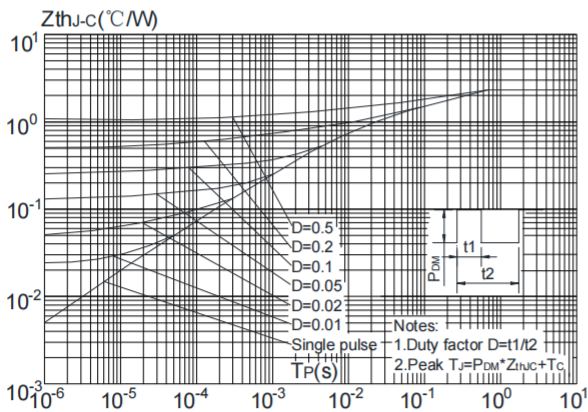
**Figure 9: Maximum Safe Operating Area**



**Figure 10: Maximum Continuous Drain Current vs. Case Temperature**



**Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case**



Test Circuit

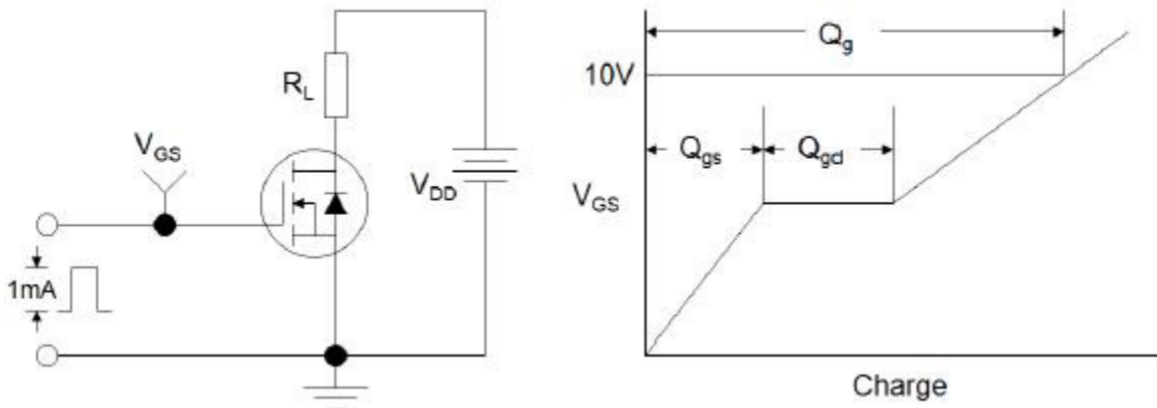


Figure1:Gate Charge Test Circuit & Waveform

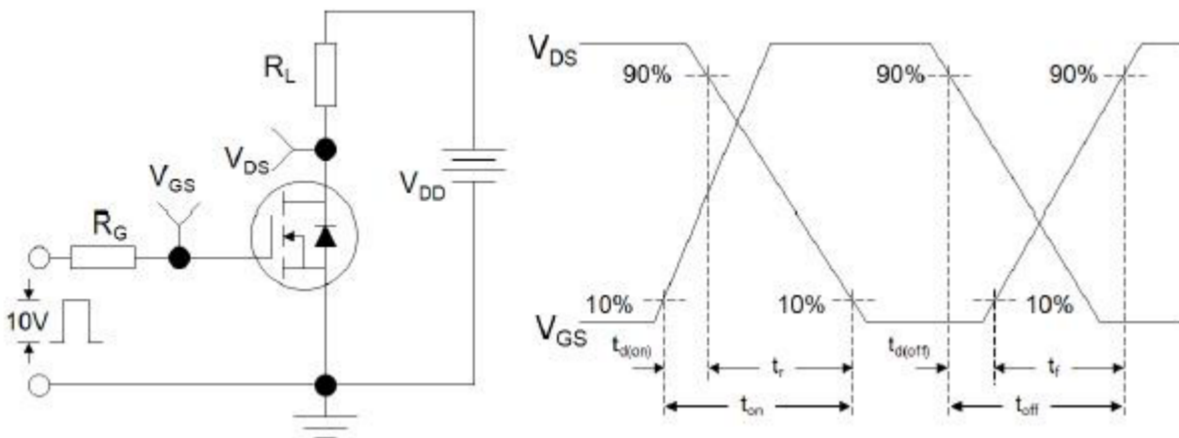


Figure 2: Resistive Switching Test Circuit & Waveforms

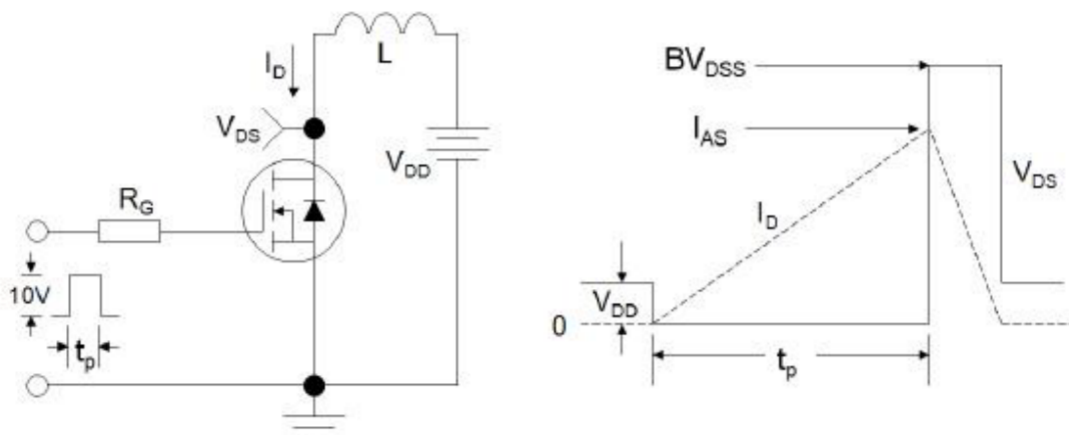


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

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